

Silicon PNP Power Transistors

2N6132 2N6133 2N6134

DESCRIPTION

- With TO-220 package
- High power dissipation
- Complement to NPN type :
 2N6129 2N6130 2N6131

APPLICATIONS

- Power amplifier and medium speed switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

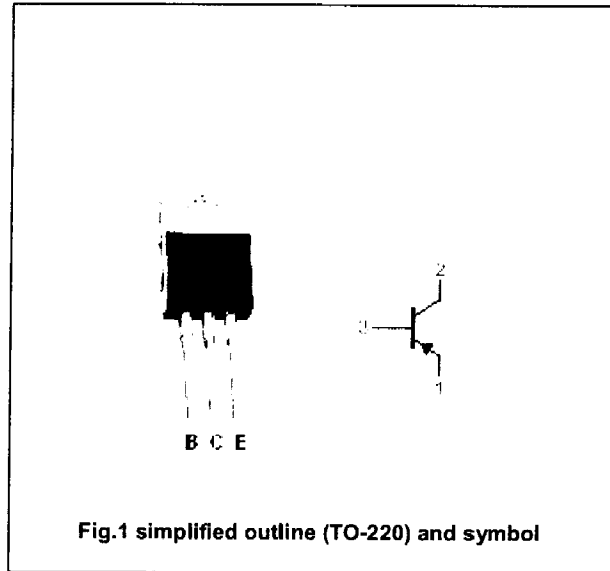


Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CB0}	Collector-base voltage	2N6132	-40	V
		2N6133	-60	
		2N6134	-80	
V _{CEO}	Collector-emitter voltage	2N6132	-40	V
		2N6133	-60	
		2N6134	-80	
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-7	A
I _B	Base current		-3	A
P _T	Total power dissipation	T _C =25	50	W
T _J	Junction temperature		150	
T _{stg}	Storage temperature		-65~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{thjc}	Thermal resistance from junction to case	2.5	°W

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